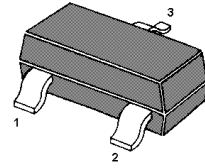


BFS20

NPN Silicon Epitaxial Planar Transistor

High frequency transistor for IF and VHF applications



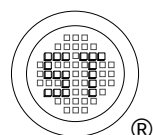
1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	25	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 7\text{ mA}$	h_{FE}	40	-	140	-
Collector Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	-	100	μA
Base Emitter Voltage at $V_{CE} = 10\text{ V}$, $I_C = 7\text{ mA}$	V_{BE}	-	-	0.9	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_C = 5\text{ mA}$, $f = 100\text{ MHz}$	f_T	275	450	-	MHz
Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	1		pF



Dated : 11/11/2006